

**REMARKS**

Review and reconsideration on the merits are requested.

In response to the objection to the disclosure, a more descriptive Title of the Invention is presented herein for the Examiner's consideration. Withdrawal of the objection is respectfully requested.

Claim 1 has been amended to correct the informality noted by the Examiner.

Claim 1 has been amended to recite that the gate electrode consists of a metal. Support is found, for example, at page 4, lines 21-22 of the specification. Claim 1 has also been amended to recite that the gate oxide film consists of a metal oxide obtained by oxidizing a gate electrode material between the gate electrode and the gate insulation layer. Support is found, for example, bridging pages 4-5 of the specification.

Withdrawn method claim 9 has been amended to include all of the limitations of product claim 1. Upon allowance of product claim 1, the Examiner is respectfully requested to rejoin withdrawn method claims 9-14 pursuant to MPEP § 821.04.

Claims 1-8 were rejected under 35 U.S.C. § 103(a) as being unpatentable over Figure 1 (AAPA) in view of U.S. Patent No. 6,207,472 to Callegari et al.

Applicants traverse, and respectfully request the Examiner to reconsider in view of the amendment to the claims and the following remarks.

The subject invention defined by the present claim 1 is directed to "An organic semiconductor element, comprising:

an organic semiconductor layer as a current channel;

a gate insulation layer consisting of an insulating material of an organic compound;  
a gate electrode consisting of a metal and opposing to said semiconductor layer so that  
said gate insulation layer is interposed between said gate electrode and said semiconductor layer;  
a source electrode and a drain electrode electrically connected in the vicinity of the two  
ends of the organic semiconductor layer respectively; and  
a gate oxide film consisting of a metal oxide obtained by oxidizing a gate electrode  
material oxide between said gate electrode and said gate insulation layer."

An important and characteristic feature of the invention is that a gate oxide film,  
consisting of a metal oxide obtained by oxidizing a gate electrode material, is formed between a  
gate electrode and a gate insulation layer. A semiconductor element including such a gate oxide  
film has high insulation strength. This is because metal oxides generally have higher insulation  
strength than organic oxides. This is described at page 5, lines 17-24 of the specification.

On the other hand, Callegari et al. discloses inorganic oxides formed on a gate electrode  
consisting of a metal material, such as gold, silver, palladium, aluminum, copper and platinum.  
It is noted that these inorganic oxides do not include the gate electrode metal material. See  
col. 3, lines 62 *et seq.* of Callegari et al. Thus, Callegari et al. does not teach a gate oxide film  
consisting of a metal oxide obtained by oxidizing a gate electrode material as claimed.

For the above reasons, and because Callegari et al. fails to teach all of the limitations of  
the claimed invention, it is respectfully submitted that the present claims are patentable over  
Callegari et al. and withdrawal of the foregoing rejection under 35 U.S.C. § 103(a) is respectfully  
requested.

Withdrawal of all rejections, rejoinder of withdrawn claims 9-14, and allowance of claims 1-14 is earnestly solicited.

In the event that the Examiner believes that it may be helpful to advance the prosecution of this application, the Examiner is invited to contact the undersigned at the local Washington, D.C. telephone number indicated below.

The USPTO is directed and authorized to charge all required fees, except for the Issue Fee and the Publication Fee, to Deposit Account No. 19-4880. Please also credit any overpayments to said Deposit Account.

Respectfully submitted,



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